

GW1NZ series of FPGA Products

Datasheet

DS841-1.8.1E, 11/26/2021

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Revision History

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01/23/2019	1.0E	Initial version published.		
02/12/2019	1.1E	Figures of part naming updated.		
04/03/2019	1.2E	 I/O BANK view updated; The description of I3C bus and SPMI added; the precision of the on chip OSC added; Changerd "Operating Temperature" to "Junction Temperature". 		
09/25/2019	1.3E	 The note of "GW1NZ-1 I/Os support differential output, rather than differential input" added; Power supply ramp rate modified. 		
11/06/2019	1.4E	Number of Max. I/O updated.		
01/06/2020	1.5E	 The static current of ZV devices added; Low power description of user flash added. 		
06/30/2020	1.6E	GW1NZ-1 FN32F added.		
12/12/2020	1.7E	The new device of GW1NZ-2 added.		
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11/26/2021	1.81E	I/O logic info., etc., optimized.		

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1 About This Guide 1.1 Purpose

1 About This Guide

1.1 Purpose

This data sheet describes the features, product resources and structure, AC/DC characteristics, timing specifications of the configuration interface, and the ordering information of the GW1NZ series of FPGA product. It is designed to help you understand the GW1NZ series of FPGA products quickly and select and use devices appropriately.

1.2 Related Documents

The latest user guides are available on the GOWINSEMI Website. You can find the related documents at www.gowinsemi.com:

- DS841, GW1NZ series of FPGA Products Data Sheet
- 2. <u>UG290, Gowin FPGA Products Programming and Configuration User</u> Guide
- 3. UG843, GW1NZ series of FPGA Products Package and Pinout
- 4. UG842, GW1NZ-1 Pinout

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1.3 Abbreviations and Terminology

The abbreviations and terminology used in this manual are as shown in Table 1-1 below.

Table 1-1 Abbreviations and Terminologies

Abbreviations and Terminology	Full Name	
FPGA	Field Programmable Gate Array	
CFU	Configurable Functional Unit	
CLS	Configurable Logic Section	
CRU	Configurable Routing Unit	
LUT4	Four-input Look-up Table	
LUT5	Five-input Look-up Tables	
LUT6	Six-input Look-up Tables	
LUT7	Seven-input Look-up Tables	
LUT8	Eight-input Look-up Tables	
REG	Register	
ALU	Arithmetic Logic Unit	
IOB	Input/output Bank	
BSRAM	Block Static Random Access Memory	
SP	Single Port 16K BSRAM	
SDP	Semi Dual Port 16K BSRAM	
DP	True Dual Port 16K BSRAM	
DQCE	Dynamic Quadrant Clock Enable	
DCS	Dynamic Clock Selector	
PLL	Phase Locked Loop	
SPMI	System Power Management Interface	
GPIO	Gowin Programmable IO	
CS16	WLCSP16	
FN32	QFN32	
FN32F	QFN32F	
QN48	QFN48	

1.4 Support and Feedback

Gowin Semiconductor provides customers with comprehensive technical support. If you have any questions, comments, or suggestions, please feel free to contact us directly using the information provided below.

Website: www.gowinsemi.com
E-mail: support@gowinsemi.com

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2 General Description 2.1 Features

2General Description

The GW1NZ series of FPGA products are the first generation products in the LittleBee® family. They offer ultra-low power consumption, instant on, low cost, non-volatile, high security, various packages, and flexible usage. They can be widely used in communication, industry control, consumer, video control, etc.

GOWINSEMI provides a new generation of FPGA hardware development environment through market-oriented independent research and development that supports the GW1NZ series of FPGA products and applies to FPGA synthesizing, layout, place and routing, data bitstream generation and download, etc.

2.1 Features

- Zero power consumption
 - 55nm embedded flash technology
 - LV: Supports 1.2V core voltage
 - ZV: Supports 0.9V core voltage. Please refer to Table 4-10_Static Supply Current (ZV Device) for the lowest power consumption.
 - Clock dynamically turns on and off
 - User Flash dynamically turns on and off
- Power Management Module (GW1NZ-1)
 - SPMI: System power management interface
 - VCC and VCCM are independent in the device
- User Flash (GW1NZ-1)
 - Dynamically turns on and off
 - 64K bits
 - Data Width: 32
 - 10,000 write cycles
 - Greater than ten years' data retention at +85 ℃
 - Supports page erasure: 2048 bytes per page
 - Duration: Max. 25ns
 - Electric current
 - a). Read Operation: 2.19 mA/25 ns (Vcc) & 0.5 mA/25 ns (Vccx) (MAX);
 - b). Write operation/erase operation: 12/12 mA (MAX)
 - Quick page erasure/Write operation

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2 General Description 2.1 Features

- Clock frequency: 40MHz
- Write operation time: ≤16µs
- Page erasure time: ≤120 ms
- Multiple I/O Standards
 - GW1NZ-1: LVCMOS33/25/18/15/12; LVTTL33; PCI;
 LVDS25E, BLVDSE, MLVDSE, LVPECLE, RSDSE
 - Input hysteresis option
 - Supports 4mA,8mA,16mA,24mA, etc. drive options
 - Slew Rate option
 - Output drive strength option
 - Individual Bus Keeper, Weak Pull-up, Weak Pull-down, and Open Drain option
 - Hot Socket
 - I3C hard core, supports SDR mode
 - Support differential output, rather than differential input
- Abundant Slices
 - Four input LUT (LUT4)
 - Double-edge flip-flops
 - Supports shifter register
 - Supports shadow SRAM
- Block SRAM with multiple modes
 - Supports Dual Port, Single Port, and Semi Dual Port
 - Supports bytes write enable
- Flexible PLLs
 - Frequency adjustment (multiplication and division) and phase adjustment
 - Supports global clock
- Built-in Flash programming
 - Instant-on
 - Supports security bit operation
 - Supports AUTO BOOT and DUAL BOOT
- Configuration
 - JTAG configuration
 - Offers up to six GowinCONFIG configuration modes: AUTOBOOT, SSPI, MSPI, CPU, SERIAL, and DUAL BOOT

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2 General Description 2.2 Product Resources

2.2 Product Resources

Table 2-1 Product Resources

Device	GW1NZ-1
LUT4	1,152
Register	864
Shadow SRAM (bits)	4K
Block SRAM (bits)	72K
PLLs	1
User Flash (bits)	64K
Max. I/O	48
Core Voltage (LV)	1.2V
Core Voltage (ZV)	0.9V

2.3 Package Information

Table 2-2 Package Information and Max. User I/O

Package	Pitch (mm)	Size (mm)	GW1NZ-1
FN32	0.4	4 x 4	25
FN32F	0.4	4 x 4	25
CS16	0.4	1.8 x 1.8	11
QN48	0.4	6 x 6	40

Note!

- In this manual, abbreviations are employed to refer to the package types. See 5.1 Part Name.
- JTAGSEL_N and JTAG pins cannot be used as I/O simultaneously. The Max. I/O noted in this table is referred to when the four JTAG pins (TCK, TDI, TDO, and TMS) are used as I/O. When mode [2:0] = 001, JTAGSEL_N and the four JTAG pins (TCK, TDI, TDO, and TMS) can be used as GPIO simultaneously, and the Max. user I/O is increased by one.

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3 Architecture 3.1 Architecture Overview

3 Architecture

3.1 Architecture Overview

Figure 3-1 GW1NZ-1 Architecture Overview

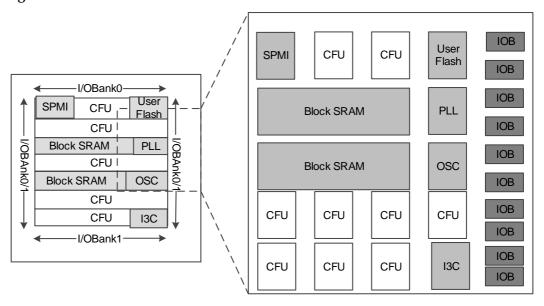


Figure 3-1 shows the GW1NZ devices architecture view. The core of the GW1NZ devices is the array of logic unit surrounded by IO blocks. GW1NZ also provides BSRAM, PLL, user Flash, and on chip oscillator and supports Instant-on. SPMI and I3C are also embedded in the GW1NZ devices. See Table 2-1 for more detailed information on internal resources.

Configurable Function Unit (CFU) is the base cell for the array of the GW1NZ series of FPGA Products. These CFUs arrange in rows and columns. CFU can be configured as LUT4 mode, ALU mode, and memory mode. See 3.2 Configurable Function Unit for further detailed information.

The I/O resources in the GW1NZ series of FPGA products are arranged around the periphery of the devices in groups referred to as banks, including Bank0 and Bank1. The I/O resources support multiple level standards, and support basic mode, SRD mode, and generic DDR mode. See 3.3 IOB for further detailed information.

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The BSRAM is embedded as a row in the GW1NZ series of FPGA products. In the FPGA array, each BSRAM occupies three columns of CFU. Each BSRAM has 18,432 bits (18 Kbits) and supports multiple configuration modes and operation modes. See <u>3.6 Block</u> SRAM (BSRAM) for further detailed information.

The User Flash is embedded in the GW1NZ series of FPGA products, without loss of data even if power off. See Table 2-1 for further detailed information. See <u>3.7</u> User Flash (GW1NZ-1).

GW1NZ provides one PLL. PLL blocks provide the ability to synthesize clock frequencies. Frequency adjustment (multiplication and division), phase adjustment, and duty cycle can be adjusted using the configuration of parameters. See <u>3.8 Clock</u> for further detailed information.

FPGA provides abundant CRUs, connecting all the resources in FPGA. For example, routing resources distributed in CFU and IOB connect resources in CFU and IOB. Routing resources can automatically be generated by Gowin software. In addition, the GW1NZ series of FPGA Products also provide abundant GCLKs, long wires (LW), global set/reset (GSR), and programming options, etc. See <u>3.9Long</u> Wire (LW), <u>3.10Global</u> Set/Reset (GSR), <u>3.11Programming</u> Configuration for further detailed information.

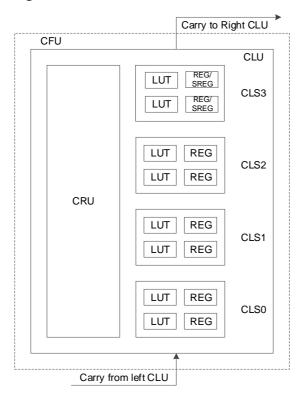
3.2 Configurable Function Unit

The configurable function unit and the configurable logic unit are two basic units for FPGA core of GOWINSEMI. As shown in Figure 3-2, each unit consists of four configurable logic sections and its configurable routing unit. Each of the three configurable logic sections contains two 4-input LUTs and two registers, and the other one only contains two 4-input LUTs.

Configurable logical sections in CLU cannot be configured as SRAM, but as basic logic, ALU, and ROM. The configurable logic sections in the CFU can be configured as basic logic, ALU, SRAM, and ROM depending on the applications. This section takes CFU as an example to introduce CFU and CLU.

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Figure 3-2 CFU View



Note!

- SREG needs special patch supporting. Please contact Gowin technical support or lo cal Office for this patch.
- In GW1NZ-2, the CLK, CE, and SR of CLS3 and CLS2 are driven by the same source.

3.2.1 CLU

The CLU supports three operation modes: Basic logic mode, ALU mode, and ROM mode.

Basic Logic Mode

Each LUT can be configured as one four-input LUT. Higher input number of LUT can be formed by combining the LUT4 together.

- Each CLS can form one five-input LUT5.
- Two CLSs can form one six-input LUT6.
- Four CLSs can form one seven-input LUT7.
- Eight CLSs (two CLUs) can form one eight-input LUT8.

ALU Mode

When combined with carry chain logic, the LUT can be configured as the ALU mode to implement the following functions.

- Adder and subtractor
- Up/down counter
- Comparator, including greater-than, less-than, and not-equal-to
- MULT
- Memory mode

In this mode, a 16 x 4 S-SRAM or ROM can be constructed by using

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CLSs.

This SRAM can be initialized during the device configuration stage.
 The initialization data can be generated in the bit stream file from Gowin software.

Register

Each Configurable Logic Section (CLS) has two registers (REG), as shown in Figure 3-3 below.

Figure 3-3 Register in CFU

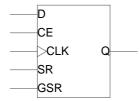


Table 3-1 Register Description in CFU

Signal	I/O	Description	
D	I	Data input ¹	
CE	I	CLK enable, can be high or low effective ²	
CLK	I	Clock, can be rising edge or falling edge trigging ²	
SR	I	Set/Reset, can be configured as ² : Synchronized reset Synchronized set Asynchronous reset Non	
GSE ^{3,4}	1	Global Set/Reset, can be configured as ⁴ : Asynchronous reset Asynchronous set Non	
Q	0	Register	

Note!

- [1] The source of the signal D can be the output of a LUT, or the input of the CRU; as such, the register can be used alone when LUTs are in use.
- [2] CE/CLK/SR in CFU is independent.
- [3] In the GW1NZ series of FPGA products, GSR has its own dedicated network.
- [4] When both SR and GSR are effective, GSR has higher priority.

3.2.2 CRU

The main functions of the CRU are as follows:

- Input selection: Select input signals for the CFU.
- Configurable routing: Connect the input and output of the CFUs, including inside the CFU, CFU to CFU, and CFU to other functional blocks in FPGA.

3.3 IOB

The IOB in the GW1NZ series of FPGA products includes IO buffer, IO logic, and its routing unit. As shown in Figure 3-4, each IOB connects to

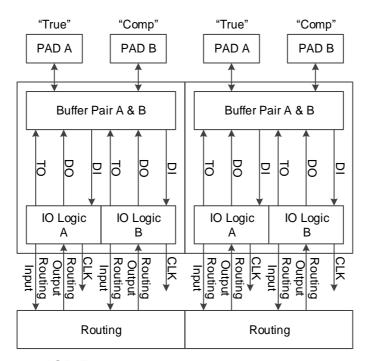
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two Pins (Marked as A and B). As input, they can be used as a single-end signal; as output, they can be used as an output differential pair or as a single end input/output.

Note!

GW1NZ-1 I/Os support differential output, rather than differential input.

Figure 3-4 IOB Structure View



IOB Features:

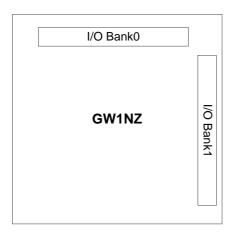
- VCCO supplied with each bank
- Supports multiple levels: LVCMOS, PCI, LVTTL, etc.
- Input hysteresis option
- Output drive strength option
- Slew Rate option
- Individual Bus Keeper, Weak Pull-up, Weak Pull-down, and Open Drain option
- Hot Socket
- IO Logic supports basic mode, SRD mode, and generic DDR mode
- I3C hard core embedded, supports SDR mode
- Supports differential output, rather than differential input

3.3.1 I/O Buffer

GW1NZ-1 includes Bank0 and Bank1, as shown in Figure 3-5. Each Bank has independent Vcco. It can be 3.3V, 2.5V, 1.8V, 1.5V, or 1.2V.

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Figure 3-5 I/O Bank Distribution of GW1NZ-1



GW1NZ series FPGA products contain both LV and UV. LV devices support 1.2V core voltage to meet users' low power needs. ZV devices support 0.9V core voltage. Zero-power consumption can be available for ZV devices. VCCO supplied with I/O Bank can be set as 1.2V, 1.5V, 1.8V, 2.5V, or 3.3V according to requirements. Vccx supports 1.8V, 2.5 V, and 3.3 V power supply.

Note!

By default, the Gowin Programmable IO is tri-stated weak pull-up.

For the V_{CCO} requirements of different I/O standards, see Table 3-2 and Table 3-3.

Table 3-2 Output I/O Types and Configuration Options of GW1NZ-1

I/O Type (Output)	Single/Differ	Bank Vcco (V)	Driver Strength (mA)
LVCMOS33/LVTTL 33	Single	3.3	8/24/16/12/4
LVCMOS25	Single	2.5	8/16/12/4
LVCMOS18	Single	1.8	8/12/4
LVCMOS15	Single	1.5	8/4
LVCMOS12	Single	1.2	8/4
PCI33	Single	3.3	8/4
LVCMOS33D	Differential	3.3	8/24/16/12/4
LVCMOS25D	Differential	2.5	8/16/12/4
LVCMOS18D	Differential	1.8	8/12/4
LVCMOS15D	Differential	1.5	8/4
LVCMOS12D	Differential	1.2	8/4

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Table 3-3 Input I/O Types and Configuration Options of GW1NZ-1 $\,$

I/O Type (Input)	Single/Differ	Bank V _{CCO} (V)	HYSTERESIS	Need V _{REF}
LVCMOS33/LVTTL 33	Single	1.2/1.5/1.8/2.5/3.3	Yes	No
LVCMOS25	Single	1.2/1.5/1.8/2.5/3.3	Yes	No
LVCMOS18	Single	1.2/1.5/1.8/2.5/3.3	Yes	No
LVCMOS15	Single	1.2/1.5/1.8/2.5/3.3	Yes	No
LVCMOS12	Single	1.2/1.5/1.8/2.5/3.3	Yes	No
PCI33	Single	3.3	Yes	No
LVCMOS33OD25	Single	2.5	Yes	No
LVCMOS330D18	Single	1.8	Yes	No
LVCMOS330D15	Single	1.5	Yes	No
LVCMOS250D18	Single	1.8	Yes	No
LVCMOS250D15	Single	1.5	Yes	No
LVCMOS180D15	Single	1.5	Yes	No
LVCMOS150D12	Single	1.2	Yes	No
LVCMOS25UD33	Single	3.3	Yes	No
LVCMOS18UD25	Single	2.5	Yes	No
LVCMOS18UD33	Single	3.3	Yes	No
LVCMOS15UD18	Single	1.8	Yes	No
LVCMOS15UD25	Single	2.5	Yes	No
LVCMOS15UD33	Single	3.3	Yes	No
LVCMOS12UD15	Single	1.5	Yes	No
LVCMOS12UD18	Single	1.8	Yes	No
LVCMOS12UD25	Single	2.5	Yes	No
LVCMOS12UD33	Single	3.3	Yes	No

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3.3.2 I/O Logic

Figure 3-6 shows the I/O logic output of the GW1NZ series of FPGA products.

Figure 3-6 I/O Logic Output

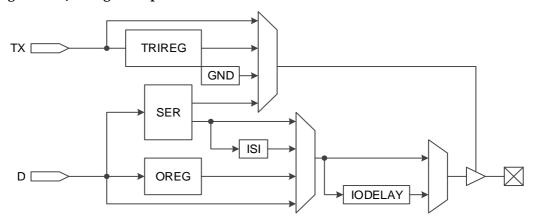


Figure 3-7 shows the I/O logic input of the GW1NZ series of FPGA products.

Figure 3-7 I/O Logic Input

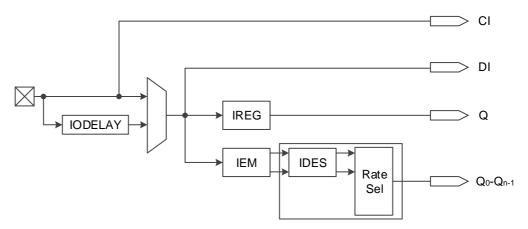


Table 3-4 Port Description

Ports	I/O	Description
CI ^[1]	Input	GCLK input signal. For the number of GCLK input signals, please refer to <u>UG842</u> , <u>GW1NZ-1 Pinout</u> .
DI	Input	IO port low-speed input signal, entering into Fabric directly.
Q	Output	IREG output signal in SDR module.
Q ₀ -Q _{n-1}	Output	IDES output signal in DDR module.

Note!

When CI is used as GCLK input, DI, Q, and Q_0 - Q_{n-1} cannot be used as I/O input and output.

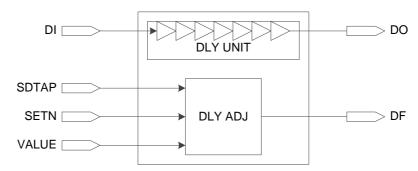
A description of the I/O logic modules of the GW1NZ series of FPGA products is presented below:

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IODELAY

See Figure 3-8 for an overview of the IODELAY. Each I/O of the GW1NZ series of FPGA products has an IODELAY cell. A total of 128(0~127) step delay is provided, with one-step delay time of about 30ps.

Figure 3-8 IODELAY



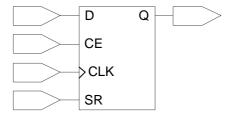
There are two ways to control the delay cell:

- Static control
- Dynamic control: usually used to sample delay window together with IEM. The IODELAY cannot be used for both input and output at the same time

I/O Register

See Figure 3-9 for the I/O register in the GW1NZ series of FPGA products. Each I/O provides one input register, INFF, one output register, OUTFF, and a tristate Register, TCFF.

Figure 3-9 Register Structure in I/O Logic



Note!

- CE can be either active ow (0: enable)or active high (1: enable).
- CLK can be either rising edge trigger or falling edge trigger.
- SR can be either synchronous/asynchronous SET or RESET or disable.
- The register can be programmed as register or latch.

IEM

IEM is for sampling clock edge and is used in the generic DDR mode, as shown in Figure 3-10.

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3 Architecture 3.4 I3C Bus (GW1NZ-1)

Figure 3-10 IEM Structure



De-serializer DES and Clock Domain Transfer

The GW1NZ series of FPGA products provide a simple DES for each input I/O to support advanced I/O protocols.

Serializer SER

The GW1NZ series of FPGA products provide a simple Serializer SER for each output I/O to support advanced I/O protocols.

3.3.3 I/O Logic Modes

The I/O Logic in the GW1NZ series of FPGA products supports several modes. In each operation, the I/O can be configured as output, input, and INOUT or tristate output (output signal with tristate control).

The GW1NZ-1 pins IOR6 (A,B,C....J) do not support IO logic.

For further information about I/O logic modes, please refer to <u>UG289</u>, Gowin Programmable IO (GPIO) User Guide.

3.4 I3C Bus (GW1NZ-1)

3.4.1 Overview

GW1NZ series of FPGA products includes a hard core of I3C bus controller, which supports SDR mode. The I3C controller is backwards compatible with I2C features low power, and is high speed and extensible. The I3C bus is compliant with MIPI I3C protocol, adopts register interfaces, and supports operation modes of I3C SDR Master and I3C SDR Slave.

I3C SDR Master

- Compliance with MIPI I3C protocol;
- Supports I3C address arbitration detection;
- Supports Single Data Rate (SDR) mode:
- The max. data transmission rate can up to 12.5Mbps;
- Start / Stop / Repeated Start / Acknowledge generation;
- Start / Stop / Repeated Start detection;
- Support dynamically allocating address via SETDASA or ENTDAA;
- Supports Receive/Send data;
- Supports In-band Interrupts;
- Supports Hot-Join;
- Supports dynamically allocating address when hot-join;
- Supports CCC's command;
- Supports dynamic adjusting SCL frequency;
- Compatible with I2C Slave:
- Adopts register interfaces.

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3 Architecture 3.4 I3C Bus (GW1NZ-1)

I3C SDR Slave

- Compliance with MIPI I3C protocol;
- Start / Acknowledge generation;
- Start / Stop / Repeated Start detection;
- Support dynamically allocating address via SETDASA or ENTDAA;
- Receive/Send data;
- Send an IBI or hot-join request. If more than one slaves send the IBI or hot-join requests, the min. address obtains the arbitration;
- Static address of Slave configuration;
- Adopts register interfaces.

3.4.2 Port Signal

For the detailed information about I3C port signals, working principle, timing, and examples, please refer to <u>IPUG508-1.2 Gowin I3C SDR IP</u> User Guide.

Table 3-5 I3C Port Signals

Port Name	I/O	Description
AAC	Input	The setting to clear ACK response, single pulse signal
AAO	output	Output ACK signal
AAS	Input	Set ACK response, single pulse signal
ACC	Input	The setting to clear continuous operation mode, single pulse signal
ACKHS	Input	Set ACK high-level time
ACKLS	Input	Set ACK low-level time
ACO	output	Continuous operation mode output
ACS	Input	Set continuous operation mode, single pulse signal
ADDRS	Input	Set slave address
CE	Input	Clock enable signal
CLK	Input	Clock input
CMC	Input	Clear the current Master role, single pulse signal
СМО	output	Output the flag of current master role
CMS	Input	Set the current Master role, single pulse signal
DI[7:0]	Input	Data input
DO[7:0]	output	Data output
DOBUF[7:0]	output	Buffer data output
LGYC	Input	Clear the setting of I2C as the current communication object, single pulse signal
LGYO	output	Output of I2C as the current communication object
LGYS	Input	Set I2C as the current communication object, single pulse signal
PARITYERROR	output	Parity error signal
RECVDHS	Input	Set high-level time of receiving data

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3 Architecture 3.5 SPMI (GW1NZ-1)

Port Name	I/O	Description
RECVDLS	Input	Set low-level time of receiving data
RESET	Input	Asynchronous reset, active high
SCLI	Input	I3C serial clock input
SCLO	output	I3C serial clock line
SCLOEN	output	I3C serial clock output enable
SCLPULLO	output	I3C serial clock pullup output
SCLPULLOEN	output	I3C serial clock pullup output enable
SDAI	Input	I3C serial data input
SDAO	output	I3C serial data output
SDAOEN	output	I3C serial data output enable
SDAPULLO	output	I3C serial data pullup output
SDAPULLOEN	output	I3C serial data pullup output enable
SENDAHS	Input	Set high-level time of sending address
SENDALS	Input	Set low-level time of sending address
SENDDHS	Input	Set high-level time of sending data
SENDDLS	Input	Set low-level time of sending data
SIC	Input	Signal of clearing interrupt flag
SIO	output	Signal of output signal interrupt
STRTC	Input	Setting of clearing the START command, single pulse signal
STRTO	output	Output START command
STRTS	Input	Set START command, single pulse signal
STATE	output	Output internal state
STRTHDS	Input	Set the holding time of the START command
STOPC	Input	Clear the STOP command setting, single pulse signal
STOPO	output	Output the STOP command
STOPS	Input	Set the STOP command, single pulse signal
STOPSUS	Input	Set the setting time of the STOP command
STOPHDS	Input	Set the holding time of the STOP command

3.5 SPMI (GW1NZ-1)

3.5.1 Overview

The GW1NZ series of FPGA products provides SPMI and the SPMI controller IP. As a Master, the GW1NZ device supports for the power management of the external Slave devices via the SPMI interface. As a Slave, it also supports for the FPGA power management.

The GW1NZ series of FPGA products supports two ways to control the main power:

 Using hardware I/O VCCEN: The main power is turned off when VCCEN is 0. The main power is on when VCCEN is 1;

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 Sending the command of shut down by Master: Master sends reset / sleep / wakeup to recover FPGA main power. The main power can also be recovered at low pulse of SPMI_EN.

Note!

For the detailed information of operation modes, communication modes, commands, and timing, etc, please refer to *IPUG529*, *Gowin SPMI User Guide*.

3.5.2 Port Signal

Table 3-6 SPMI Port Signal

Name	I/O	Description
SPMI_EN	input	SPMI enable signal
SPMI_CLK	intput	System clock signal
SPMI_SCLK	inout	SPMI serial clock signal
SPMI_SDATA	inout	SPMI serial data signal

3.6 Block SRAM (BSRAM)

3.6.1 Introduction

GW1NZ series FPGA products provide abundant SRAM. The Block SRAM (BSRAM) is embedded as a row in the FPGA array and is different from S-SRAM (Shadow SRAM). Each BSRAM occupies three columns of CFU in the FPGA array. Each BSRAM has 18,432 bits (18Kbits). There are five operation modes: Single Port, Dual Port, Semi-dual Port, ROM, and FIFO.

An abundance of BSRAM resources provide a guarantee for the user's high-performance design. BSRAM features:

- Max.18,432 bits per BSRAM
- BSRAM itself can run at 170MHz at max (typical, Read-before-write is 100MHz)
- Single Port
- Dual Port
- Semi-dual Port
- Parity bits
- ROM
- Data width from 1 to 36 bits
- Mixed clock mode
- Mixed data width mode
- Enable Byte operation for double byte or above
- Normal read and write mode
- Read-before-write mode
- Write-through Mode

3.6.2 Configuration Mode

The BSRAM mode in the GW1NZ series of FPGA products supports different data bus widths. See Table 3-7.

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Single Port Mode	Dual Port Mode ^[1]	Semi-Dual Port Mode
16K x 1	16K x 1	16K x 1
8K x 2	8K x 2	8K x 2
4K x 4	4K x 4	4K x 4
2K x 8	2K x 8	2K x 8
1K x 16	1K x 16	1K x 16
512 x 32	-	512 x 32
2K x 9	2K x 9	2K x 9
1K x 18	1K x 18	1K x 18
512 x 36	-	512 x 36

Table 3-7 Memory Size Configuration

Note!

[1] The GW1NZ-1 device does not support Dual Port Mode.

Single Port Mode

In the single port mode, BSRAM can write to or read from one port at one clock edge. During the write operation, the data can show up at the output of BSRAM. Normal-Write Mode and Write—through Mode can be supported. When the output register is bypassed, the new data will show at the same write clock rising edge.

For further information about Single Port Block Memory ports and the related description, please refer to <u>UG285</u>, <u>Gowin BSRAM & SSRAM User Guide</u>.

Dual Port Mode

BSRAM support dual port mode. The applicable operations are as follows:

- Two independent read
- Two independent write
- An independent read and an independent write at different clock frequencies

For further information about Dual Port Block Memory ports and the related description, please refer to <u>UG285</u>, <u>Gowin BSRAM & SSRAM User Guide</u>..

Semi-Dual Port Mode

Semi-Dual Port supports read and write at the same time on different ports, but it is not possible to write and read to the same port at the same time. The system only supports write on Port A, read on Port B.

For further information about Semi-Dual Port Block Memory ports and the related description, please refer to UG285, Gowin BSRAM & SSRAM User Guide...

Read Only

BSRAM can be configured as ROM. The ROM can be initialized during

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the device configuration stage, and the ROM data needs to be provided in the initialization file. Initialization completes during the device power-on process.

Each BSRAM can be configured as one 16 Kbits ROM. For further information about Read Only Port Block Memory ports and the related description, please refer to <u>UG285</u>, <u>Gowin BSRAM & SSRAM User Guide</u>...

3.6.3 Mixed Data Bus Width Configuration

BSRAM in the GW1NZ series of FPGA products supports mixed data bus width operation. In the dual port and semi-dual port modes, the data bus width for read and write can be different. For the configuration options that are available, please see Table 3-8 and Table 3-9 below.

Table 3-8 Dual Port Mixed Read/Write Data Width Configuration

Read	Write Port						
Port	16K x 1	8K x 2	4K x 4	2K x 8	1K x 16	2K x 9	1K x 18
16K x 1	*	*	*	*	*		
8K x 2	*	*	*	*	*		
4K x 4	*	*	*	*	*		
2K x 8	*	*	*	*	*		
1K x 16	*	*	*	*	*		
2K x 9						*	*
1K x 18						*	*

Note!

Table 3-9 Semi Dual Port Mixed Read/Write Data Width Configuration

Read	Write Por	Write Port							
Port	16K x 1	8K x 2	4K x 4	2K x 8	1K x 16	512 x 32	2K x 9	1K x 18	512 x 36
16K x 1	*	*	*	*	*	*			
8K x 2	*	*	*	*	*	*			
4K x 4	*	*	*	*	*	*			
2K x 8	*	*	*	*	*	*			
1K x 16	*	*	*	*	*	*			
512 x 32	*	*	*	*	*	*			
2K x 9							*	*	*
1K x 18							*	*	*

Note!

3.6.4 Byte-enable

The BSRAM in the GW1NZ series of FPGA products supports byte-enable. For data longer than a byte, the additional bits can be blocked,

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[&]quot;*"denotes the modes supported.

[&]quot;*" denotes the modes supported.

and only the selected portion can be written into. The blocked bits will be retained for future operation. Read/write enable ports (WREA, WREB), and byte-enable parameter options can be used to control the BSRAM write operation.

3.6.5 Parity Bit

There are parity bits in BSRAMs. The 9th bit in each byte can be used as a parity bit to check the correctness of data transmission. It can also be used for data storage.

3.6.6 Synchronous Operation

- All the input registers of BSRAM support synchronous write;
- The output registers can be used as pipeline register to improve design performance:
- The output registers are bypass-able.

3.6.7 Power up Conditions

BSRAM initialization is supported when powering up. During the power-up process, BSRAM is in standby mode, and all the data outputs are "0". This also applies in ROM mode.

3.6.8 BSRAM Operation Modes

BSRAM supports five different operations, including two read operations (Bypass Mode and Pipeline Read Mode) and three write operations (Normal Write Mode, Write-through Mode, and Read-before-write Mode).

Read Mode

Read data from the BSRAM via output registers or without using the registers.

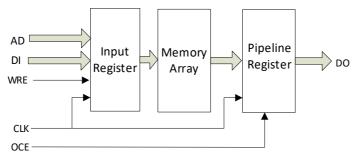
Pipeline Mode

While writing in the BSRAM, the output register and pipeline register are also being written. The data bus can be up to 36 bits in this mode.

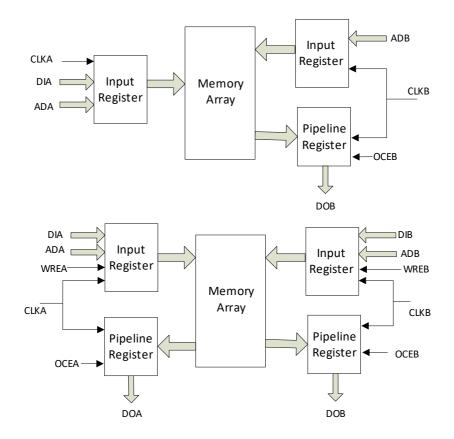
Bypass Mode

The output register is not used. The data is kept in the output of memory array.

Figure 3-11 Pipeline Mode in Single Port, Dual Port and Semi Dual Port



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Write Mode

NORMAL WRITE MODE

In this mode, when the user writes data to one port, and the output data of this port does not change. The data written in will not appear at the read port.

WRITE-THROUGH MODE

In this mode, when the user writes data to one port, and the data written in will also appear at the output of this port.

READ-BEFORE-WRITE MODE

In this mode, when the user writes data to one port, and the data written in will be stored in the memory according to the address. The original data in this address will appear at the output of this port.

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3.6.9 Clock Operations

Table 3-10 lists the clock operations in different BSRAM modes:

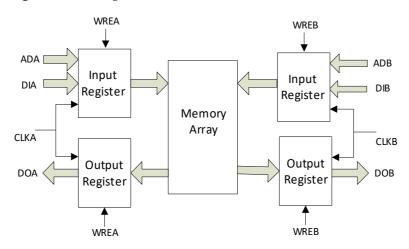
Table 3-10 Clock Operations in Different BSRAM Modes

Clock Operations	Dual Port Mode	Semi-Dual Port Mode	Single Port Mode
Independent Clock Mode	Yes	No	No
Read/Write Clock Mode	Yes	Yes	No
Single Port Clock Mode	No	No	Yes

Independent Clock Mode

Figure 3-12 shows the independent clocks in dual port mode with each port with one clock. CLKA controls all the registers at Port A; CLKB controls all the registers at Port B.

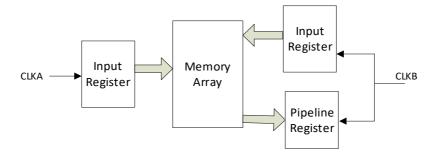
Figure 3-12 Independent Clock Mode



Read/Write Clock Operation

Figure 3-13 shows the read/write clock operations in the semi-dual port mode with one clock at each port. The write clock (CLKA) controls Port A data inputs, write address and write enable signals. The read clock (CLKB) controls Port B data output, read address, and read enable signals.

Figure 3-13 Read/Write Clock Mode

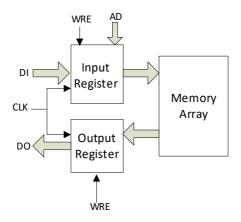


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Single Port Clock Mode

Figure 3-14shows the clock operation in single port mode.

Figure 3-14 Single Port Clock Mode



3.7 User Flash (GW1NZ-1)

3.7.1 Introduction

GW1NZ-1 offers User Flash, the features are shown below:

- 10,000 write cycles
- Capacity: 64K bits
- Greater than ten years' data retention at +85 $\,^{\circ}\mathrm{C}$
- Supports page erasure: 2,048 bytes per page
- Quick page erasure/Write operation
- Clock frequency: 40MHz
- Write operation time: ≤16µs
- Page erasure time: ≤120 ms
- Electric current
- Read Operation: 2.19 mA/25 ns (V_{CC}) & 0.5 mA/25 ns (V_{CCX}) (MAX).
- Write operation/erase operation: 12/12 mA(MAX)

3.7.2 Mode

The User Flash in GW1NZ series of FPGA products contains two modes: Normal mode and sleep mode.

- Normal mode: User flash is turned on by default. Users can perform erase/write/read operations after the device is power on. It cannot be turned off.
- Sleep mode: User flash is turned off by default to save power. Users
 can turn on/turn off the user flash mode using "Sleep" port. When the
 user flash is turned on, it's the same as the normal mode user flash,
 and users can perform erase/write/read operations.

The GW1NZ LV/ZV devices with different speeds offer different user flash modes. For further detailed information, please refer to Table 3-11.

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3 Architecture 3.8 Clock

Mode	Default Status	Turn on/Turn off	Device Version	Speed Grade
			LV	C6/I5
Normal mode On	On	No	LV	C5/I4
			ZV	C5/I4
Sleep mode Off	Voc	ZV	12	
	OII	Yes	∠v	13

Table 3-11 User Flash Modes

For further information about the user Flash in GW1NZ-1, please refer to UG295, Gowin User Flash User Guide.

3.8 Clock

For further detailed information, please refer to <u>UG286, Gowin Clock</u> <u>User Guide</u>.

3.8.1 Global Clock

The GCLK is distributed in GW1NZ-1 as two quadrants, L and R. Each quadrant provides eight GCLKs. Each GCLK has 12 optional clock sources. The optional clock resources of GCLK can be pins or CRU. Users can employ dedicated pins as clock resources to achieve better timing.

3.8.2 PLL

GW1NZ-1

PLL (Phase-locked Loop) is one kind of a feedback control circuit. The frequency and phase of the internal oscillator signal is controlled by the external input reference clock.

PLL blocks provide the ability to synthesize clock frequencies. Frequency adjustment (multiplication and division), phase adjustment, and duty cycle can be adjusted by configuring the parameters.

See Figure 3-15 for the PLL structure.

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3 Architecture 3.8 Clock

IDSEL[5:0] ODSEL[5:0] 16 **∤**6 LOCK > LOCK IDIV CLKIN [PFD > CLKOUT VCODIV VCO ICP CLKFB [CLKOUTP FBDIV LPF PS&DCA CLKOUTD3 FBDSEL[5:0] SDIV CLKOUTD

RESET_P DUTYDA[3:0] PSDA[3:0] FDLY[3:0]

Figure 3-15 PLL Structure

Table 3-12 PLL Ports Definition

Port Name	Signal	Description
CLKIN[5:0]	1	Reference clock input
CLKFB	1	Feedback clock input
RESET	1	PLL reset
RESET_P	1	PLL Power Down
IDSEL [5:0]	1	Dynamic IDIV control: 1~64
FBDSEL [5:0]	1	Dynamic FBDIV control:1~64
PSDA [3:0]	1	Dynamic phase control (rising edge effective)
DUTYDA [3:0]	1	Dynamic duty cycle control (falling edge effective)
FDLY[3:0]	1	CLKOUTP dynamic delay control
1 DE1[0.0]	1	Clock output with no phase and duty cycle
CLKOUT	Output	adjustment
CLKOUTP	Output	Clock output with phase and duty cycle adjustment
CLKOUTD	Output	Clock divider from CLKOUT and CLKOUTP (controlled by SDIV)
CLKOUTD3	Output	clock divider from CLKOUT and CLKOUTP (controlled by DIV3 with the constant division value 3)
LOCK	Output	PLL lock status: 1 locked, 0 unlocked

The PLL reference clock source can come from an external PLL pin or from internal routing GCLK, HCLK, or general data signal. PLL feedback signal can come from the external PLL feedback input or from internal routing GCLK, HCLK, or general data signal.

For PLL features of GW1NZ series of FPGA products, please refer to_4.4.5 PLL Switching Characteristics.

PLL can adjust the frequency of the input clock CLKIN (multiplication and division). The formulas for doing so are as follows:

- fclkout = (fclkin*FBDIV)/IDIV;
- 2. $f_{VCO} = f_{CLKOUT}*ODIV;$
- 3. fclkoutd = fclkout/SDIV;

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3 Architecture 3.9 Long Wire (LW)

4. fpfd = fclkin/IDIV = fclkout/FBDIV.

Note!

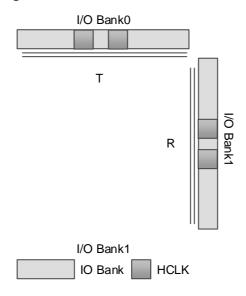
- f_{CLKIN}: The frequency of input clock CLKIN;
- fclkout: The clock frequency of CLKOUT and CLKOUTP
- f_{CLKOUTD}: The clock frequency of CLKOUTD, and CLKOUTD is the clock CLKOUT after division
- f_{PFD}: PFD Frequency, and the minimum value of f_{PFD} should be no less than 3MHz.

Adjust IDIV, FBDIV, ODIV, and SDIV to achieve the required clock frequency.

3.8.3 HCLK

HCLK is the high-speed clock in the GW1NZ series of FPGA products. It can support high-performance data transfer and is mainly suitable for source synchronous data transfer protocols. See Figure Figure 3-16. HCLK can be used for the whole I/O Bank.

Figure 3-16 GW1NZ-1 HCLK Distribution



3.9 Long Wire (LW)

As a supplement to the CRU, the GW1NZ series of FPGA products provides another routing resource, Long wire, which can be used as clock, clock enable, set/reset,or other high fan out signals.

3.10 Global Set/Reset (GSR)

A global set/reset (GSR) network is built in the GW1NZ series of FPGA product. There is a direct connection to core logic. It can be used as asynchronous/synchronous set. The registers in CFU and I/O can be individually configured to use GSR.

3.11 Programming Configuration

The GW1NZ series of FPGA products support SRAM and Flash. The Flash programming mode supports on-chip Flash and off-chip Flash. The GW1NZ series of FPGA products support DUAL BOOT, providing a

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3 Architecture 3.12 On Chip Oscillator

selection for users to backup data to off chip Flash according to requirements.

Besides JTAG, the GW1NZ series of FPGA products also supports GOWINSEMI's own configuration mode: GowinCONFIG (AUTO BOOT, SSPI, MSPI, DUAL BOOT, SERIAL, CPU, and I²C Slave). All the devices support JTAG and AUTO BOOT. For the detailed information, please refer to <u>UG290</u>, *Gowin FPGA Products Programming and Configureation User Guide*.

3.11.1 SRAM Configuration

When you adopt SRAM to configure the device, every time the device is powered on, the bit stream file needs to be downloaded to configure the device.

3.11.2 Flash Configuration

The Flash configuration data is stored in the on-chip flash. Each time the device is powered on, the configuration data is transferred from the Flash to the SRAM, which controls the working of the device. This mode can complete configuration within a few ms, and is referred to as "Quick Start". The GW1NZ series of FPGA products also support off-chip Flash configuration and dual-boot. Please refer to UG290, Gowin FPGA Products Programming and Configuration User Guide for more detailed information.

3.12 On Chip Oscillator

There is an on chip oscillator in each of the GW1NZ series of FPGA product. The on chip oscillator provides a programmable user clock with precision of $\pm 5\%$. During the configuration process, it can provide a clock for the MSPI mode. See Table 3-13 for the output frequency.

Mode	Frequency	Mode	Frequency	Mode	Frequency
0	2.5MHz ^[1]	8	7.8MHz	16	15.6MHz
1	5.4MHz	9	8.3MHz	17	17.9MHz
2	5.7MHz	10	8.9MHz	18	21MHz
3	6.0MHz	11	9.6MHz	19	25MHz
4	6.3MHz	12	10.4MHz	20	31.3MHz
5	6.6MHz	13	11.4MHz	21	41.7MHz
6	6.9MHz	14	12.5MHz	22	62.5MHz
7	7.4MHz	15	13.9MHz	23	125MHz ^[2]

Table 3-13 Oscillator Output Frequency Options

Note!

- [1] The default frequency is 2.5MHz.
- [2] 125 MHz is not suitable for MSPI.

The on-chip oscillator also provides a clock resource for user designs. Up to 64 clock frequencies can be obtained by setting the parameters. The following formula is employed to get the output clock frequency:

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3 Architecture 3.12 On Chip Oscillator

fout=250MHz/Param.

"Param" is the configuration parameter with a range of 2~128. It supports even number only.

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4 AC/DC Characteristic

4.1 Operating Conditions

4.1.1 Absolute Max. Ratings

Table 4-1 Absolute Max. Ratings

Name	Description	Min.	Max.
Vcc	Core voltage	-0.5V	1.32V
Vcco	I/O Bank Power	-0.5V	3.75V
Vccx	Auxiliary Power	-0.5V	3.75V
Storage Temperature	Storage Temperature	-65℃	+150℃
Junction Temperature	Junction Temperature	-40℃	+125℃

4.1.2 Recommended Operating Conditions

Table 4-2 Recommended Operating Conditions

Name	Description	Min.	Max.
	LV: Core Power	1.14V	1.26V
Vcc	ZV: Core Power	0.88V	1V
Vcco	I/O Bank Power	1.14V	3.6V
Vccx	Auxiliary voltage	1.71V	3.6V
Тјсом	Junction temperature Commercial operation	0℃	+85℃
TJIND	Junction temperature Industrial operation	-40℃	+100℃

Note!

For the detailed recommended operating conditions for different packages, please refer to *UG842, GW1NZ-1 Pinout*.

4.1.3 Power Supply Ramp Rates

Table 4-3 Power Supply Ramp Rates

Name	Description	Min.	Тур.	Max.
TRAMP	Power supply ramp rates for all power supplies	0.6mV/µs	-	6mV/µs

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4 AC/DC Characteristic 4.2 ESD

4.1.4 Hot Socket Specifications

Table 4-4 Hot Socket Specifications

Name	Description	Condition	I/O Type	Max.
IHS	Input or I/O leakage current	0 <v<sub>IN<v<sub>IH(MAX)</v<sub></v<sub>	I/O	150uA
I _{HS}	Input or I/O leakage current	0 <v<sub>IN<v<sub>IH(MAX)</v<sub></v<sub>	TDI, TDO, TMS,TCK	120uA

4.1.5 POR Specification

Table 4-5 POR Specification

Name	Description	Min.
5051/1	Power on reset voltage of Vcc	0.8V
POR Voltage Value	Vccx	1.5V
Value	Vcco	0.95V

4.2 ESD

Table 4-6 GW1NZ ESD - HBM

Device	GW1NZ-1
CS16	HBM>1,000V
FN32	HBM>1,000V
FN32F	HBM>1,000V
QN48	HBM>1,000V

Table 4-7 GW1NZ ESD - CDM

Device	GW1NZ-1
CS16	CDM>500V
FN32	CDM>500V
FN32F	CDM>500V
QN48	CDM>500V

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4.3 DC Characteristic

4.3.1 DC Electrical Characteristics over Recommended Operating Conditions

Table 4-8 DC Electrical Characteristics over Recommended Operating Conditions

Name	Description	Condition	Min.	Тур.	Max.
I. I.	Input or I/O	Vcco <vin<vih (max)<="" td=""><td>-</td><td>-</td><td>210 μΑ</td></vin<vih>	-	-	210 μΑ
I _{IL} ,I _{IH} leakage		0V <vin<vcco< td=""><td>-</td><td>-</td><td>10µA</td></vin<vcco<>	-	-	10µA
I _{PU}	I/O Active Pull-up Current	0 <v<sub>IN<0.7V_{CCO}</v<sub>	-30 µA	-	-150 μA
I _{PD}	I/O Active Pull-down Current	V _{IL} (MAX) <v<sub>IN<v<sub>CCO</v<sub></v<sub>	30 μΑ	-	150 μΑ
I _{BHLS}	Bus Hold Low Sustaining Current	V _{IN} =V _{IL} (MAX)	30 μΑ	-	-
Івнно	Bus Hold High Sustaining Current	V _{IN} =0.7V _{CCO}	-30 μΑ	-	-
Івньо	Bus HoldLow Overdrive Current	0≤V _{IN} ≤V _{CCO}	-	-	150 μΑ
Івнно	Bus HoldHigh Overdrive Current	0≤V _{IN} ≤V _{CCO}	-	-	-150 μA
V _{BHT}	Bus hold trigger points		VIL (MAX)	-	Vih (MIN)
C1	I/O Capacitance			5 pF	8 pF
		V _{CCO} =3.3V, Hysteresis= Large	-	482mV	-
		V _{CCO} =2.5V, Hysteresis= Large	-	302mV	-
		V _{CCO} =1.8V, Hysteresis= Large	-	152mV	-
\/. v	Hysteresis for	V _{CCO} =1.5V, Hysteresis= Large	-	94mV	-
V _{HYST}	Schmitt Trigge inputs	V _{CCO} =3.3V, Hysteresis= Small	-	240mV	-
		V _{CCO} =2.5V, Hysteresis= Small	-	150mV	-
		V _{CCO} =1.8V, Hysteresis= Small	-	75mV	-
		V _{CCO} =1.5V, Hysteresis= Small	-	47mV	-

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4.3.2 Static Current

Table 4-9 Static Supply Current (LV Device)

Name	Description	Device	Тур.
Icc	Core current (Vcc=1.2V)	GW1NZ-1	3mA
	V _{CCX} current (VCCX=3.3V)	GW1NZ-1	-
Iccx	V _{CCX} current (VCCX=2.5V)	GW1NZ-1	-
Icco	I/O Bank current (Vcco=2.5V)	GW1NZ-1	-

Table 4-10 Static Supply Current (ZV Device)

Name	Description	Device	Тур.
		GW1NZ-ZV1FN32C5/I4 GW1NZ-ZV1CS16C5/I4	50uA
Icc	GW1NZ-ZV1CS16C5/I4 GW1NZ-ZV1FN32I3 GW1NZ-ZV1FN32I2 GW1NZ-ZV1CS16I3 GW1NZ-ZV1FN32I2 GW1NZ-ZV1FN32C5/I4 GW1NZ-ZV1FN32C5/I4 GW1NZ-ZV1FN32I3 GW1NZ-ZV1FN32I3 GW1NZ-ZV1FN32I2 GW1NZ-ZV1FN32I2 GW1NZ-ZV1FN32I2 GW1NZ-ZV1FN32I2 GW1NZ-ZV1CS16I2 GW1NZ-ZV1FN32I2 GW1NZ-ZV1CS16I2 GW1NZ-ZV1CS16I3 GW1NZ-ZV1CS16I3 GW1NZ-ZV1CS16I3 GW1NZ-ZV1CS16I3 GW1NZ-ZV1FN32I3 GW1NZ-ZV1FN32I3 GW1NZ-ZV1CS16I3 GW1NZ-ZV1CS16I3	40uA	
			30uA
			0uA
	Vccx current (Vccx floating)	/ccv floating)	
1			0uA
Iccx	V _{CCX} current (VCCX=1.8V~3.3V)		1uA
			1uA
		GW1NZ-ZV1FN32I2 GW1NZ-ZV1CS16I2	1uA
	I/O Bank current (Vcco=3.3V)	GW1NZ-ZV1FN32C5/I4 GW1NZ-ZV1CS16C5/I4	0uA
Icco		GW1NZ-ZV1FN32I3 GW1NZ-ZV1CS16I3	0uA
		GW1NZ-ZV1FN32I2 GW1NZ-ZV1CS16I2	

Note!

- After device wake up, user can turn off external Vccx when they do not use user flash and chip still functional.
- The typical values in the table above are tested at room temperature.
- In zero power circumstance, if users use MODE pin, the PULL_MODE of this pin must be configured as KEEPER.

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4.3.3 I/O Operating Conditions Recommended

Table 4-11 I/O Operating Conditions Recommended

Name	Output Vo	co (V)		Input V _{REF} (V)		
Harris	Min.	Тур.	Max.	Min.	Тур.	Max.
LVTTL33	3.135	3.3	3.465	-	-	-
LVCMOS33	3.135	3.3	3.465	-	-	-
LVCMOS25	2.375	2.5	2.625	-	-	-
LVCMOS18	1.71	1.8	1.89	-	-	-
LVCMOS15	1.425	1.5	1.575	-	-	-
LVCMOS12	1.14	1.2	1.26	-	-	-
SSTL15	1.425	1.5	1.575	0.68	0.75	0.9
SSTL18_I	1.71	1.8	1.89	0.833	0.9	0.969
SSTL18_II	1.71	1.8	1.89	0.833	0.9	0.969
SSTL25_I	2.375	2.5	2.645	1.15	1.25	1.35
SSTL25_II	2.375	2.5	2.645	1.15	1.25	1.35
SSTL33_I	3.135	3.3	3.465	1.3	1.5	1.7
SSTL33_II	3.135	3.3	3.465	1.3	1.5	1
HSTL18_I	1.71	1.8	1.89	0.816	0.9	1.08
HSTL18_II	1.71	1.8	1.89	0.816	0.9	1.08
HSTL15	1.425	1.5	1.575	0.68	0.75	0.9
PCI33	3.135	3.3	3.465	-	-	-
LVPECL33E	3.135	3.3	3.465	-	-	-
MLVDS25E	2.375	2.5	2.625	-	-	-
BLVDS25E	2.375	2.5	2.625	-	-	-
RSDS25E	2.375	2.5	2.625	-	-	-
LVDS25E	2.375	2.5	2.625	-	-	-
SSTL15D	1.425	1.5	1.575	-	-	-
SSTL18D_I	1.71	1.8	1.89	-	-	-
SSTL18D_II	1.71	1.8	1.89	-	-	-
SSTL25D_I	2.375	2.5	2.625	-	-	-
SSTL25D_II	2.375	2.5	2.625	-	-	-
SSTL33D_I	3.135	3.3	3.465	-	-	-
SSTL33D_II	3.135	3.3	3.465	-	-	-
HSTL15D	1.425	1.575	1.89	-	-	-
HSTL18D_I	1.71	1.8	1.89	-	-	-
HSTL18D_II	1.71	1.8	1.89	-	-	-

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4.3.4 Single - Ended IO DC Electrical Characteristic

Table 4-12 Single - Ended IO DC Electrical Characteristic

Name	VIL		ViH		Vol	Vон	loL	Іон
name	Min	Max	Min	Max	(Max)	(Min)	(mA)	(mA)
			2.0V			Vcco-0.4V	4	-4
		0.8V					8	-8
LVCMOS33	-0.3V			3.6V	0.4V		12	-12
LVTTL33	-0.3 V	0.6 V					16	-16
							24	-24
					0.2V	Vcco-0.2V	0.1	-0.1
							4	-4
					0.4V	Vcco-0.4V	8	-8
LVCMOS25	-0.3V	0.7V	1.7V	3.6V	0. 4 v	V CCO-0.4 V	12	-12
							16	-16
					0.2V	Vcco-0.2V	0.1	-0.1
			0.65 x Vcco	3.6V	0.4V		4	-4
11/01/02/0	-0.3V	0.35 x Vcco				Vcco0.4V	8	-8
LVCMOS18							12	-12
					0.2V	Vcco-0.2V	0.1	-0.1
		0.35 x V _{CCO}	0.65 x V _{cco}	3.6V	0.4V	V _{CCO} -0.4V	4	-4
LVCMOS15	-0.3V				0.4 V		8	-8
					0.2V	V _{CCO} -0.2V	0.1	-0.1
	-0.3V	0.35 x V _{CCO}	0.65 x V _{cco}	3.6V	0.4V	V _{CCO} -0.4V	2	-2
LVCMOS12							6	-6
					0.2V	V _{CCO} -0.2V	0.1	-0.1
PCI33	-0.3V	0.3 x Vcco	0.5 x Vcco	3.6V	0.1 x Vcco	0.9 x Vcco	1.5	-0.5
SSTL33_I	-0.3V	V _{REF} -0.2V	V _{REF} +0.2V	3.6V	0.7	Vcco-1.1V	8	-8
SSTL25_I	-0.3V	V _{REF} -0.18V	V _{REF} +0.18V	3.6V	0.54V	V _{CCO} -0.62V	8	-8
SSTL25_II	-0.3V	V _{REF} -0.18V	V _{REF} +0.18V	3.6V	N/A	N/A	N/A	N/A
SSTL18_II	-0.3V	V _{REF} -0.125V	V _{REF} +0.125V	3.6V	N/A	N/A	N/A	N/A
SSTL18_I	-0.3V	V _{REF} -0.125V	V _{REF} +0.125V	3.6V	0.40V	Vcco-0.40V	8	-8
SSTL15	-0.3V	V _{REF} -0.1V	V _{REF} + 0.1V	3.6V	0.40V	Vcco-0.40V	8	-8
HSTL18_I	-0.3V	V _{REF} -0.1V	V _{REF} + 0.1V	3.6V	0.40V	Vcco-0.40V	8	-8
HSTL18_II	-0.3V	V _{REF} -0.1V	V _{REF} + 0.1V	3.6V	N/A	N/A	N/A	N/A
HSTL15_I	-0.3V	V _{REF} -0.1V	V _{REF} + 0.1V	3.6V	0.40V	Vcco-0.40V	8	-8
HSTL15_II	-0.3V	V _{REF} -0.1V	V _{REF} + 0.1V	3.6V	N/A	N/A	N/A	N/A

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4.4 Switching Characteristic

4.4.1 CFU Block Internal Timing Parameters

Table 4-13 CFU Block Internal Timing Parameters

Name	Description	Speed	Unit		
ivanie	Description	Min	Max	Offit	
tLUT4_CFU	LUT4 delay	-	0.674	ns	
tLUT5_CFU	LUT5 delay	-	1.388	ns	
tlut6_cfu	LUT6 delay	-	2.01	ns	
tlut7_cfu	LUT7 delay	-	2.632	ns	
tLUT8_CFU	LUT8 delay	-	3.254	ns	
tsr_cfu	Set/Reset to Register output	-	1.86	ns	
tco_cfu	Clock to Register output	-	0.76	ns	

4.4.2 Clock and I/O Switching Characteristics

Table 4-14 Clock and I/O Switching Characteristics

Name	Descri	Device	-5		-6		Unit
ivairie	ption		Min	Max	Min	Max	Offic
Clocks	TBD	TBD	TBD	TBD	TBD	TBD	
Pin-LUT-Pin Delay	TBD	TBD	TBD	TBD	TBD	TBD	
General I/O Pin Parameters	TBD	TBD	TBD	TBD	TBD	TBD	

4.4.3 BSRAM Switching Characteristics

Table 4-15 BSRAM Internal Timing Parameters

Name	Description	Speed	Speed Grade		
Ivallie	Description	Min	Max	Unit	
t _{COAD_BSRAM}	Clock to output from read address/data	-	5.10	ns	
tcoor_bsram	Clock to output from output register	-	0.56	ns	

4.4.4 On chip Oscillator Output Frequency

Table 4-16 On chip Oscillator Output Frequency

Name	Description	Min.	Тур.	Max.
	Output Frequency (0 to 85℃)	106.25MHz	125MHz	143.75MHz
f _{MAX}	Output Frequency (-40 to +100°C)	100MHz	125MHz	150MHz
t _{DT}	Output Clock Duty Cycle	43%	50%	57%
topjit	Output Clock Period Jitter	0.01UIPP	0.012UIPP	0.02UIPP

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4.4.5 PLL Switching Characteristics

Table 4-17 PLL Switching Characteristics

Device	LV/ZV	Speed Grade	Name	Min.	Max.
		C6/I5	CLKIN	3MHZ	400MHZ
			PFD	3MHZ	400MHZ
		C0/15	VCO	400MHZ	800MHZ
	LV		CLKOUT	3.125MHZ	400MHZ
	LV		CLKIN	3MHZ	320MHZ
		C5/I4	PFD	3MHZ	320MHZ
		C5/14	VCO	320MHZ	640MHZ
			CLKOUT	2.5MHZ	360MHZ
	ZV	C5/I4	CLKIN	3MHZ	200MHZ
GW1NZ-1			PFD	3MHZ	200MHZ
			VCO	200MHZ	400MHZ
			CLKOUT	1.5625MHZ	200MHZ
		13	CLKIN	3MHZ	150MHZ
			PFD	3MHZ	150MHZ
	ZV	13	VCO	150MHZ	300MHZ
			CLKOUT	1.171875MHZ	150MHZ
			CLKIN	3MHZ	100MHZ
		12	PFD	3MHZ	100MHZ
			VCO	100MHZ	200MHZ
			CLKOUT	0.78125MHZ	100MHZ

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4.5 User Flash Characteristic

4.5.1 DC Characteristic

Table 4-18 GW1NZ-1 User Flash DC Characteristics

Name	Parame	Max.		Linit	Wake-up	Condition		
Name	ter	Vcc ^[3]	Vccx	Unit	Time	Condition		
Read mode (w/l 25ns) ^[1]		2.19	0.5	mA	N/A	Min. Clcok period, duty cycle 100%, VIN = "1/0"		
Write mode	I _{CC1} ^[2]	0.1	12	mA	N/A			
Erase mode	ICC1 ¹ ¹	0.1	12	mA	N/A			
Page Erasure Mode		0.1	12	mA	N/A			
Read mode static current (25-50ns)	Icc2	980	25	μА	N/A	XE=YE=SE="1", between T=Tacc and T=50ns, I/O=0mA; later than T=50ns, read mode is turned off, and I/O current is the current of standby mode.		
Standby mode	IsB	5.2	20	μΑ	0	Vss, Vccx, and Vcc		
Floating mode ^[3]	I _{PD}	0	0	μA	7us	V _{CCX} =0		
Typical Value (Room temperature: 25℃)								
Standby mode	IsB	0.4	7.5	μA	0	Vss, Vccx, and Vcc		
Floating mode ^[3]	I _{PD}	0	0	μΑ	3.5us	Vccx=0		

Note!

- [1] Means the average current, and the peak value is higher than the average one.
- [2] Calculated in different T_{new} clock periods.
 - T_{new}< T_{acc} is not allowed
 - T_{new} = T_{acc}
 - $T_{acc} < T_{new} 50ns: I_{CC1} (new) = (I_{CC1} I_{CC2})(T_{acc}/T_{new}) + I_{CC2}$
 - T_{new} >50ns: Icc1 (new) = (Icc1 Icc2)($T_{\text{acc}}/T_{\text{new}}$) + 50ns x Icc2/ T_{new} + IsB
 - t > 50ns, $I_{CC2} = I_{SB}$
- [3] Only supported in user flash in sleep mode.

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4.5.2 Timing Parameters[1],[5],[6]

Table 4-19 User Flash Timing Parameters

User Modes	Parameter	Name	Min.	Max.	Unit
	WC1		-	25	ns
	TC		-	22	ns
Access time ^[2]	ВС	T _{acc} ^[3]	-	21	ns
	LT		-	21	ns
	WC		-	25	ns
Program/Erase	e to data storage	T _{nvs}	5	-	μs
Data storage h	old time	T _{nvh}	5	-	μs
Data storage h	old time (Overall erase)	T _{nvh1}	100	-	μs
Time from data setup	a storage to program	T _{pgs}	10	-	μs
Program hold t	time	T_{pgh}	20	-	ns
Write time		T _{prog}	8	16	μs
Write ready tim	ne	T _{wpr}	>0	-	ns
Erase hold time	е	T _{whd}	>0	-	ns
Time from cont setup	trol signal to write/Erase	T _{cps}	-10	-	ns
Time from SE t	to read setup	Tas	0.1	-	ns
E pulse high le	evel time	T _{pws}	5	-	ns
Adress/data se	etup time	T _{ads}	20	-	ns
Adress/data ho	old time	T _{adh}	20	-	ns
Data hold-up ti	me	T _{dh}	0.5	-	ns
	WC1	Tah	25	-	ns
Read mode	TC		22	-	ns
address hold	ВС		21	-	ns
time ^[3]	LT		21	-	ns
	WC		25	-	ns
SE pulse low le	evel time	T _{nws}	2	-	ns
Recovery time		T _{rcv}	10	-	μs
Data storage ti	Data storage time			6	ms
Erasure time	T _{erase}	100	120	ms	
Overall erase t	T _{me}	100	120	ms	
Wake-up time standby mode	T _{wk_pd}	7	-	μs	
Standby hold to	ime	T _{sbh}	100	-	ns
Vcc setup time		T _{ps}	0	-	ns
V _{CCX} hold time		T _{ph}	0	-	ns

Note!

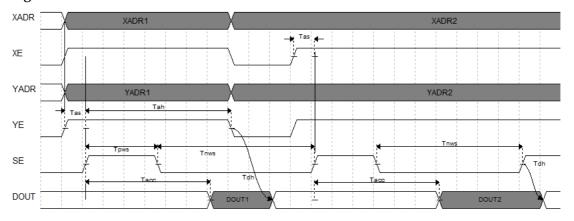
- [1] The parameter values may change;
- [2] The values are simulation data only.

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- [3]After XADR, YADR, XE, and YE are valid, T_{acc} start time is SE rising edge. DOUT is kept until the next valid read operation;
- [4]T_{hv} is the time between write and the next erasure. The same address can not be written twice before erasure, so does the same register. This limitation is for safety;
- [5]Both the rising edge time and falling edge time for all waveform is 1ns;
- [6] TX, YADR, XE, and YE hold time need to be T_{acc} at leaset, and T_{acc} start from SE rising edge.

4.5.3 Operation Timing Diagrams

Figure 4-1 Read Mode



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SE
ERASE

XADR

XADR

XADR

XADR

XADR

YADR1

YADR2

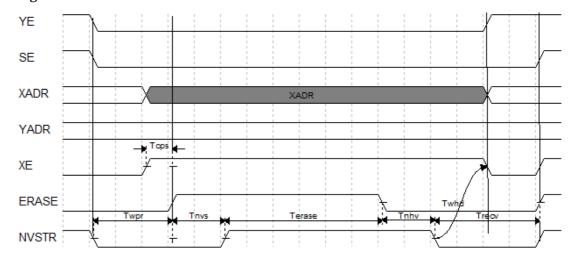
YADR2

YADR3

YADR

Figure 4-2 Write Mode





4.6 Configuration Interface Timing Specification

The GW1NZ series of FPGA products GowinCONFIG support six configuration modes: AUTO BOOT, DUAL BOOT, MSPI, SSPI, SERIAL, and CPU. For more detailed information, please refer to <u>UG290</u>, <u>Gowin FPGA Products Programming and Configuration User Guide</u>.

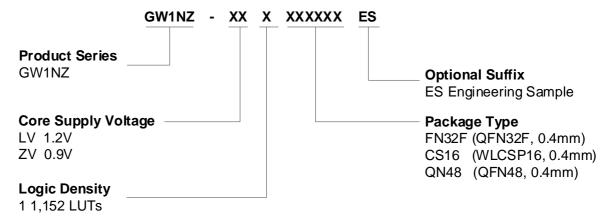
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5 Ordering Information 5.1 Part Name

5 Ordering Information

5.1 Part Name

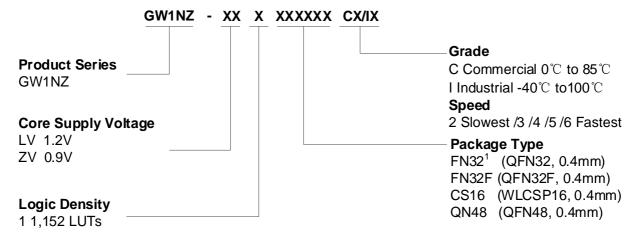
Figure 5-1 Part Naming Example-ES



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5 Ordering Information 5.2 Package Mark

Figure 5-2 Part Naming Example-Production



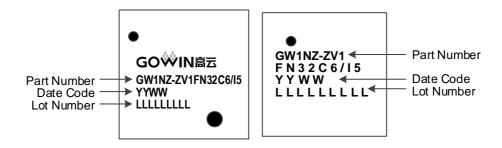
Note!

- [1] FN32 is the legacy version.
- For the further detailed information about the package type and pin number, please refer to 2.2 Product Resources and 2.3 Package Information.
- The LittleBee[®] family devices and Arora family devices of the same speed level have different speed.
- Both "C" and "I" are used in partial GW1NZ device part name marking. GOWIN devices are screened using industrial standards, so one same device can be used for both industrial (I) and commercial (C) applications. The maximum temperature of the industrial grade is 100°C, and the maximum temperature of the commercial grade is 85°C. Therefore, if the same chip meets the speed level 5 in the commercial grade application, the speed level is 4 in the industrial grade application.

5.2 Package Mark

The device information of GOWINSEMI is marked on the chip surface, as shown in Figure 5-3.

Figure 5-3 Package Mark



Note!

The first two lines in the right figure above are the "Part Number".

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